

TOSHIBA Power Transistor Module
Silicon PNP Triple Diffused Type (Four Darlington Power Transistors in One)

MP4009

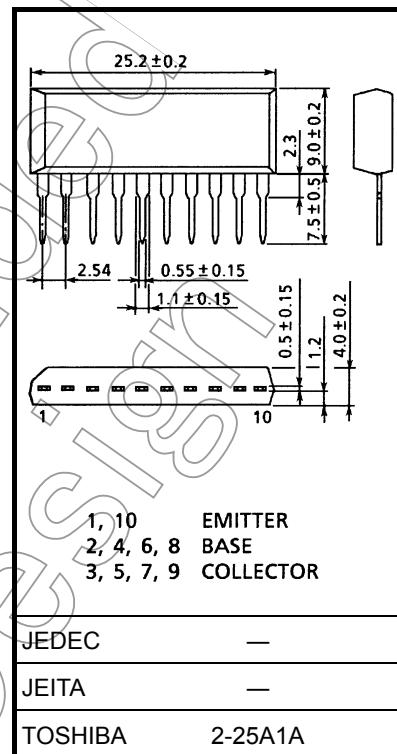
High Power Switching Applications

Hammer Drive, Pulse Motor Drive

Inductive Load Switching

Industrial Applications

Unit: mm



Absolute Maximum Ratings (Ta = 25°C)

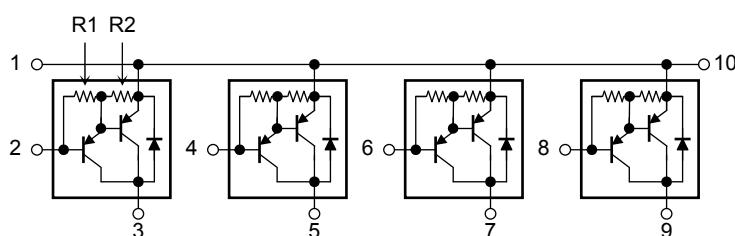
Characteristics	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	-100	V
Collector-emitter voltage	V _{CEO}	-100	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	DC	I _C	A
	Pulse	I _{CP}	
Continuous base current	I _B	-0.1	A
Collector power dissipation (1 device operation)	P _C	2.0	W
Collector power dissipation (4 devices operation)	P _T	4.0	W
Junction temperature	T _j	150	°C
Storage temperature range	T _{stg}	-55 to 150	°C

Weight: 2.1 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Array Configuration



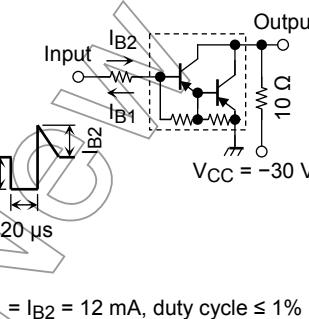
R1 ≈ 5 kΩ, R2 ≈ 120 Ω

Thermal Characteristics

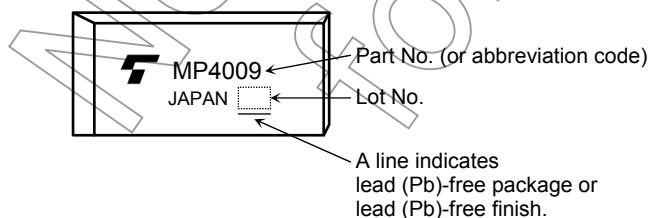
Characteristics	Symbol	Max	Unit
Thermal resistance from junction to ambient (4-device operation, $T_a = 25^\circ\text{C}$)	$\Sigma R_{\text{th}} (\text{j-a})$	31.3	$^\circ\text{C/W}$
Maximum lead temperature for soldering purposes (3.2 mm from case for 10 s)	T_L	260	$^\circ\text{C}$

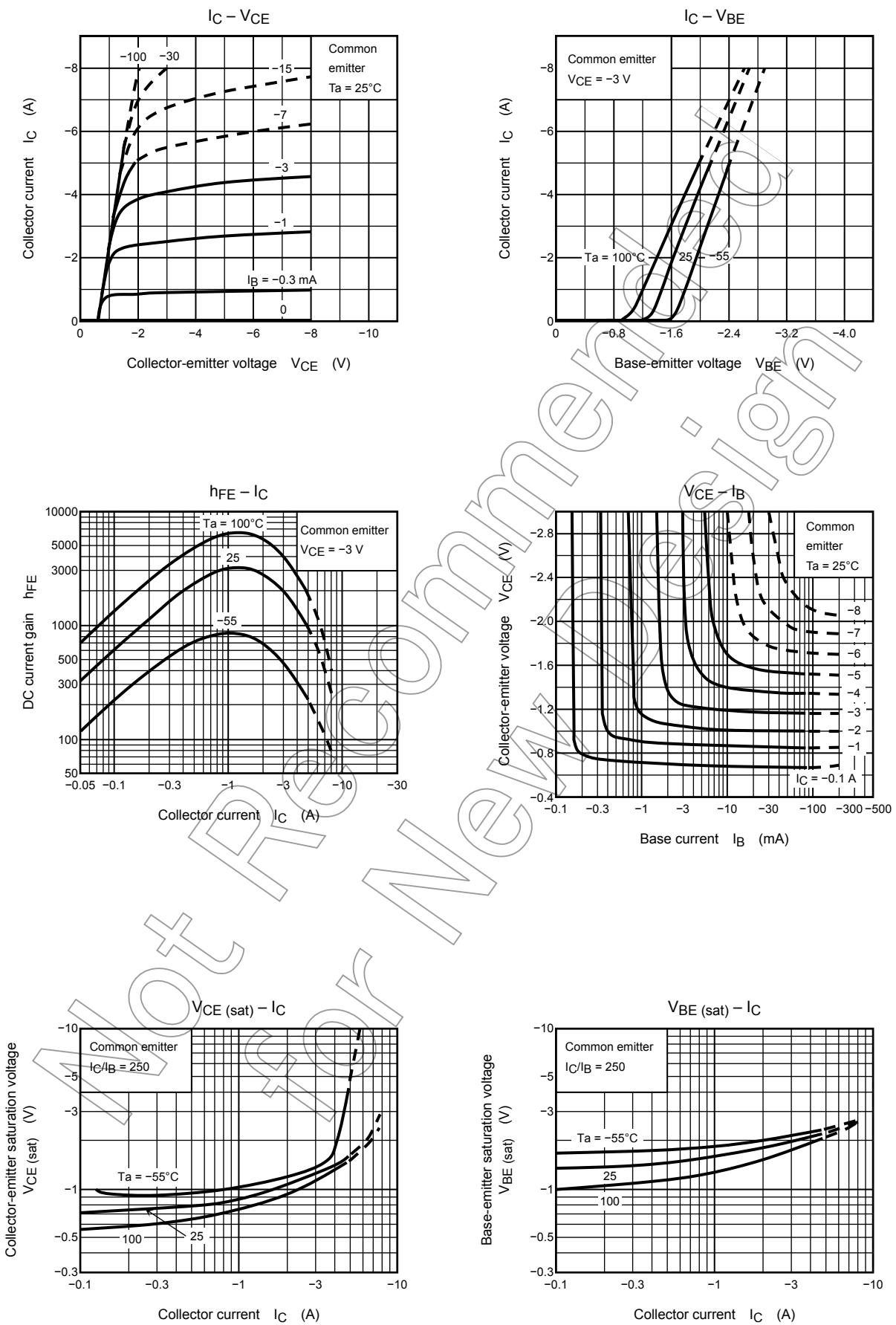
Electrical Characteristics ($T_a = 25^\circ\text{C}$)

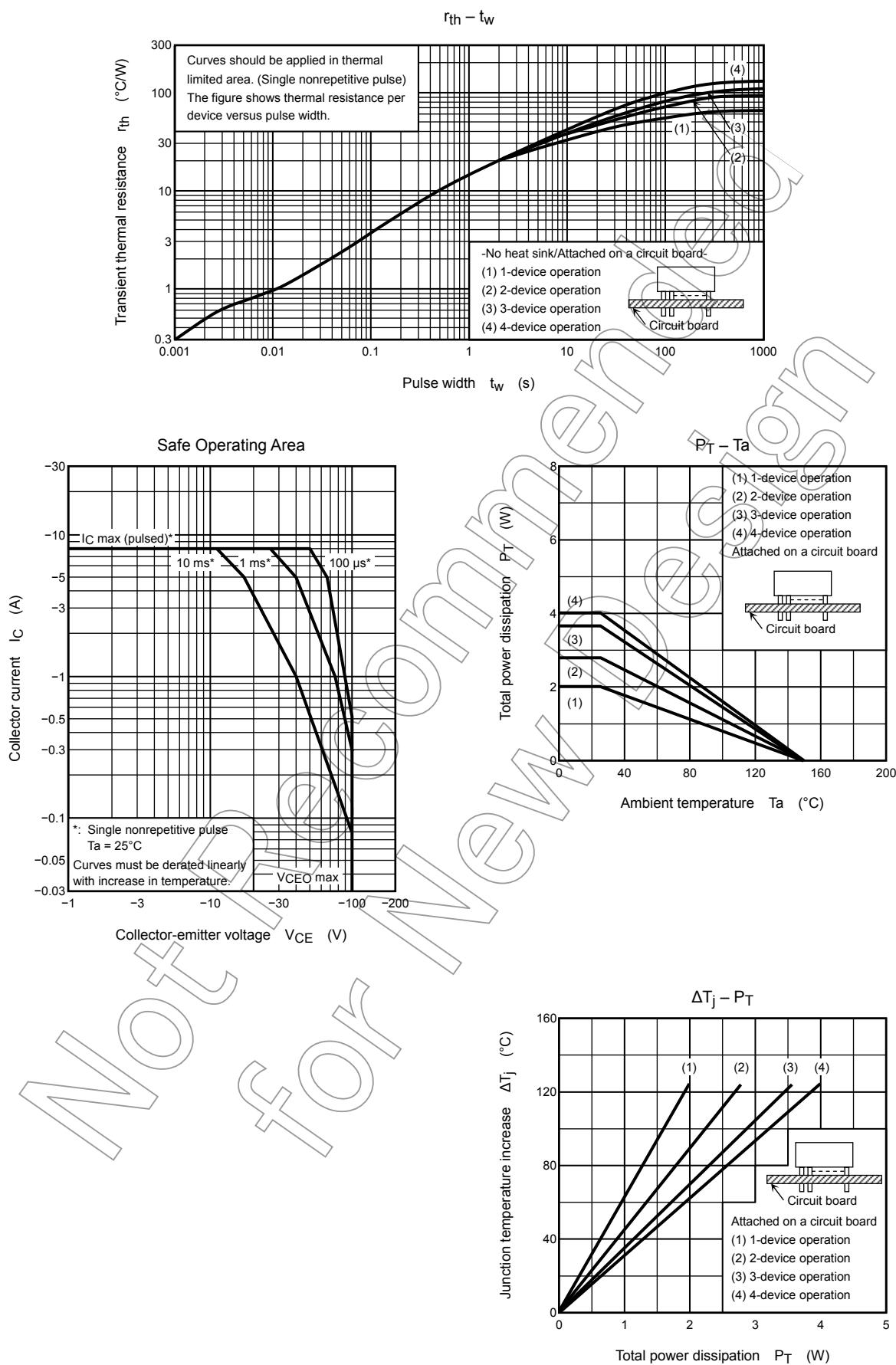
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{\text{CB}} = -100 \text{ V}, I_{\text{E}} = 0 \text{ A}$	—	—	-10	μA
Collector cut-off current	I_{CEO}	$V_{\text{CE}} = -100 \text{ V}, I_{\text{B}} = 0 \text{ A}$	—	—	-10	μA
Emitter cut-off current	I_{EBO}	$V_{\text{EB}} = -5 \text{ V}, I_{\text{C}} = 0 \text{ A}$	-0.3	—	-2.0	mA
Collector-base breakdown voltage	$V_{(\text{BR}) \text{ CBO}}$	$I_{\text{C}} = -1 \text{ mA}, I_{\text{E}} = 0 \text{ A}$	-100	—	—	V
Collector-emitter breakdown voltage	$V_{(\text{BR}) \text{ CEO}}$	$I_{\text{C}} = -30 \text{ mA}, I_{\text{B}} = 0 \text{ A}$	-100	—	—	V
DC current gain	$h_{\text{FE}} (1)$	$V_{\text{CE}} = -3 \text{ V}, I_{\text{C}} = -0.5 \text{ A}$	1000	—	—	—
	$h_{\text{FE}} (2)$	$V_{\text{CE}} = -3 \text{ V}, I_{\text{C}} = -3 \text{ A}$	1000	—	—	—
Saturation voltage	$V_{\text{CE}} (\text{sat})$	$I_{\text{C}} = -3 \text{ A}, I_{\text{B}} = -12 \text{ mA}$	—	—	-2.0	V
	$V_{\text{BE}} (\text{sat})$	$I_{\text{C}} = -3 \text{ A}, I_{\text{B}} = -12 \text{ mA}$	—	—	-2.5	
Transition frequency	f_T	$V_{\text{CE}} = -3 \text{ V}, I_{\text{C}} = -0.5 \text{ A}$	3	—	—	MHz
Collector output capacitance	C_{ob}	$V_{\text{CB}} = 50 \text{ V}, I_{\text{E}} = 0 \text{ A}, f = 1\text{MHz}$	—	40	—	pF
Switching time	Turn-on time	t_{on}	—	0.5	—	μs
	Storage time	t_{stg}	—	3.0	—	
	Fall time	t_f	—	2.0	—	



Marking







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20070701-EN

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